

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L16	2084	(348/294,308).CCLS	US-PGPUB; USPAT	OR	OFF ²	2008/05/23 12:18
S5	7936	((voltage with gate with transistor with read\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 15:10
S6	5698	((voltage near6 gate) with transistor with read\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 15:11
S7	501	((voltage near6 gate) near4 (chang\$4 or adjust\$4 or increas\$4 or decreas\$4 or different) with transistor with read\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 15:12
S8	667658	"348"/\$.ccls. or "250"/\$.ccls. or "257"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 15:13
S9	196	S7 and S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 15:13
S10	15790	((voltage near6 gate) near4 (chang\$4 or adjust\$4 or increas\$4 or decreas\$4 or different) with transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:04
S11	11958	((voltage near3 gate) near4 (chang\$4 or adjust\$4 or increas\$4 or decreas\$4 or different) with transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:05
S12	1521	((voltage near6 gate) near4 (chang\$4 or adjust\$4 or increas\$4 or decreas\$4 or different) with transistor with bias\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:05

SI3	265163	"348"/\$.ccls. or "250"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:05
SI4	54	SI2 and SI3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:06
SI5	282	(lin near1ye).xp.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:09
SI6	28	SI5 and bias\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:11
SI7	13618	((voltage near6 gate) near6 (first and second) with transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:17
SI8	335	SI3 and SI7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:19
SI9	3	"2001196570"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:32
S20	4	"2002064749"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:38
S21	4	"10200817"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:41
S22	3	"09307817"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 16:42
S23	4687	((gate near3 voltage) with transistor) and (imag\$4 near2 (sensor or device))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 18:05

S24	1180	((gate near3 voltage) with transistor with (chang\$4 or adjust\$4 or vary\$4 or increas\$4 or decreas\$4 or different)) and (imag \$4 near2 (sensor or device))	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 18:06
S25	20	((gate near3 voltage) with transistor with (chang\$4 or adjust\$4 or vary\$4 or increas\$4 or decreas\$4 or different)) and (imag \$4 near2 (sensor or device))	EPO; JPO	OR	ON	2008/05/22 18:06
S26	428	\$6 and Si3	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 18:12
S27	153	\$26 and holes	US- PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 18:13
S28	7	("60 51857").PN. OR ("6476371").URPN.	US- PGPUB; USPAT; USOCR	OR	ON	2008/05/22 18:18
S29	109	innotech.as.	US- PGPUB; USPAT; USOCR	OR	ON	2008/05/22 18:21
S30	0	\$29 and (mitsuida.in.)	US- PGPUB; USPAT; USOCR	OR	ON	2008/05/22 18:21
S31	27	\$29 and (Takashi.in.)	US- PGPUB; USPAT; USOCR	OR	ON	2008/05/22 18:21
S32	21	innotech.as. and (imag \$4 near2 (device or sensor))	US- PGPUB; USPAT; USOCR	OR	ON	2008/05/22 18:38
S33	9	(voltage near2 regulat \$4) and ((plural\$4 or several) near1 (voltage)) and 348/ 294- 323.ccls.	US- PGPUB; USPAT; USOCR	OR	ON	2008/05/22 18:52
S34	64	(voltage near2 generat \$4) and ((plural\$4 or several) near1 (voltage)) and 348/ 294- 323.ccls.	US- PGPUB; USPAT; USOCR	OR	ON	2008/05/22 18:55

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